

RELIABILITY REPORT
FOR
MAX7317ATE+
PLASTIC ENCAPSULATED DEVICES

February 2, 2010

MAXIM INTEGRATED PRODUCTS

120 SAN GABRIEL DR.
SUNNYVALE, CA 94086

Approved by
Ken Wendel
Quality Assurance
Director, Reliability Engineering

Conclusion

The MAX7317ATE+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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I. Device Description

A. General

The MAX7317 serial-interfaced peripheral provides microprocessors with 10 I/O ports rated to 7V. Each port can be individually configured as either an opendrain output, or an overvoltage-protected Schmitt input. The MAX7317 supports hot insertion. All port pins remain high impedance in power-down ($V_+ = 0V$) with up to 8V asserted on them. The MAX7317 is available in 16-pin thin QFN and QSOP packages and operates in the $-40^{\circ}C$ to $+125^{\circ}C$ range. For a similar part with constant-current outputs and 8-bit PWM controls, refer to the MAX6966/MAX6967 data sheet.

II. Manufacturing Information

A. Description/Function:	10-Port SPI-Interfaced I/O Expander with Overvoltage and Hot-Insertion Protection
B. Process:	S4
C. Number of Device Transistors:	
D. Fabrication Location:	California, Texas or Japan
E. Assembly Location:	China, Malaysia, Philippines, Thailand
F. Date of Initial Production:	July 24, 2004

III. Packaging Information

A. Package Type:	16-pin TQFN 3x3
B. Lead Frame:	Copper
C. Lead Finish:	100% matte Tin
D. Die Attach:	Conductive
E. Bondwire:	Au (1 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-9000-1276
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	Level 1
J. Single Layer Theta Ja:	64°C/W
K. Single Layer Theta Jc:	6.9°C/W
L. Multi Layer Theta Ja:	48°C/W
M. Multi Layer Theta Jc:	6.9°C/W

IV. Die Information

A. Dimensions:	59 X 59 mils
B. Passivation:	Si ₃ N ₄ /SiO ₂ (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Al with Ti/TiN Barrier
D. Backside Metallization:	None
E. Minimum Metal Width:	Metal1 = 0.5 / Metal2 = 0.6 / Metal3 = 0.6 microns (as drawn)
F. Minimum Metal Spacing:	Metal1 = 0.45 / Metal2 = 0.5 / Metal3 = 0.6 microns (as drawn)
G. Bondpad Dimensions:	5 mil. Sq.
H. Isolation Dielectric:	SiO ₂
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

- A. Quality Assurance Contacts: Ken Wendel (Director, Reliability Engineering)
Bryan Preeshl (Managing Director of QA)
- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.
0.1% For all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 47 \times 2} \text{ (Chi square value for MTTF upper limit)}$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 22.9 \times 10^{-9}$$

$$\lambda = 22.9 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

The following failure rate represents data collected from Maxim's reliability monitor program. Maxim performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at <http://www.maxim-ic.com/qa/reliability/monitor>. Cumulative monitor data for the S4 Process results in a FIT Rate of 0.05 @ 25C and 0.83 @ 55C (0.8 eV, 60% UCL)

B. Moisture Resistance Tests

The industry standard 85°C/85%RH or HAST testing is monitored per device process once a quarter.

C. E.S.D. and Latch-Up Testing

The DW92-2 die type has been found to have all pins able to withstand a HBM transient pulse of +/-1000 V per Mil-Std 883 Method 3015.7. Latch-Up testing has shown that this device withstands a current of +/-250 mA.

Table 1
Reliability Evaluation Test Results

MAX7317ATE+

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES
Static Life Test (Note 1)				
	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality	47	0
Moisture Testing (Note 2)				
HAST	Ta = 130°C RH = 85% Biased Time = 96hrs.	DC Parameters & functionality	77	0
Mechanical Stress (Note 2)				
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters & functionality	77	0

Note 1: Life Test Data may represent plastic DIP qualification lots.

Note 2: Generic Package/Process data